	Type	Hits	Search Text	DBs
1	BRS	3431	((light or laser or led) near3 (source or beam or diode)) with ((perturb$5 or disturb$5 or modif$7 or chang$5 or alter$5) near5 (die or area or region)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	124700	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	855	(((light or laser or led) near3 (source or beam or diode)) with ((perturb$5 or disturb$5 or modif$7 or chang$5 or alter$5) near5 (die or area or region)) and semiconductor and @ad<=20000419	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	551	(determin$5 or detect$5 or analyz$5 or inspect$5) near9 (semiconductor near3 die)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	32	(light or laser or led) near3 (source or beam or diode)) with ((perturb$5 or disturb$5 or modif$7 or chang$5 or alter$5) near5 die)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	23	(((light or laser or led) near3 (source or beam or diode)) with ((perturb$5 or disturb$5 or modif$7 or chang$5 or alter$5) near5 die)) and @ad<=2000419	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	1	(((light or laser or led) near3 (source or beam or diode)) with ((perturb$5 or disturb$5 or modif$7 or chang$5 or alter$5) near5 (die or area or region)) and ((determin$5 or detect$5 or analyz$5 or inspect$5) near9 (semiconductor near3 die))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	14	(((light or laser or led) near3 (source or beam or diode)) with ((perturb$5 or disturb$5 or modif$7 or chang$5 or alter$5) near5 (die or area or region)) and semiconductor and (@ad<=20000419) and ((semiconductor or wafer) near2 die$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	IS&R	12	(("5,056,061") or ("5,553,022") or ("5,642,307") or ("4,419,747") or ("5,056,061") or ("4,766,516")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	IS&R	2	(("5,350,715").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
11	BRS	1	(((("5,056,061") or ("5,553,022") or ("5,642,307") or ("4,419,747") or ("5,056,061") or ("4,766,516")).PN.) and ((((light or laser or led) near3 (source or beam or diode)) with ((perturb$5 or disturb$5 or modif$7 or chang$5 or alter$5)) near5 (die or area or region)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	57321	(determin$5 or detect$5 or analyz$5 or inspect$5) near5 semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS	103	((((light or laser or led) near3 (source or beam or diode)) with ((perturb$5 or disturb$5 or modif$7 or chang$5 or alter$5)) near5 (die or area or region)) and ((determin$5 or detect$5 or analyz$5 or inspect$5) near5 semiconductor) and @ad<=20000419	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	59	(((((light or laser or led) near3 (source or beam or diode)) with ((perturb$5 or disturb$5 or modif$7 or chang$5 or alter$5)) near5 (die or area or region)) and ((determin$5 or detect$5 or analyz$5 or inspect$5) near5 semiconductor) and @ad<=20000419) not (semiconductor adj laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB